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PATENT ABSTRACTS OF JAPAN

(21) Application number: **63252321**

(51) Intl. Cl.: **H01L 21/66** H01L 21/205 H01L 21/28

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(71) Applicant: **MITSUBISHI ELECTRIC CORP**

(72) Inventor: **MOMOTAKE YASUHITO**
MOCHIZUKI HIROSHI

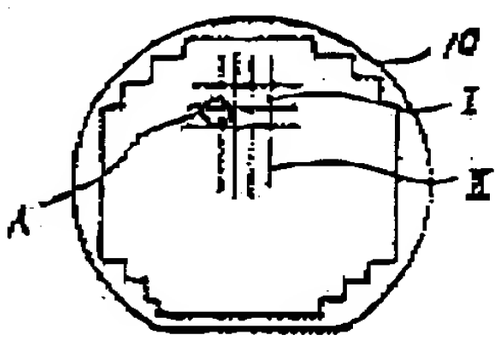
(74) Representative:

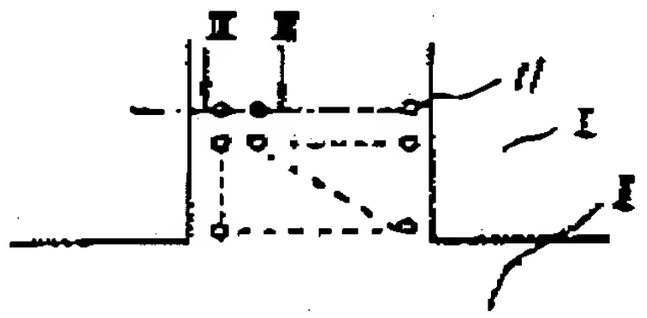
(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

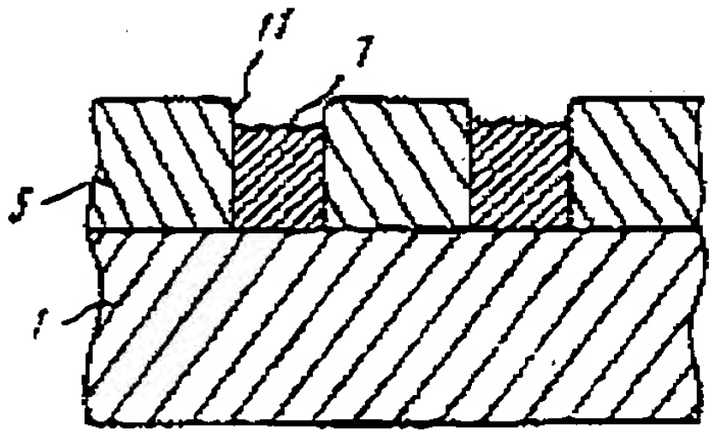
(57) Abstract:

PURPOSE: To obtain a film thickness of a desired selective growth film in an element formation region, to measure a film thickness highly accurately and to realize high reliability of a semiconductor device by a method wherein a measuring region is set on a flattened substrate and is formed to be a pattern identical to a part to be measured in the element formation region.

CONSTITUTION: In a dicing line region II, one part of a substrate 1 is opened so as to be exposed; a plane shape of a contact hole 11 used as a measuring region is made to be a size identical to a contact hole 6 which has been formed in a region I to be used as a semiconductor







device. Accordingly, the contact hole formed in the dicing line region II is formed on a that substrate 1; its structure is not complicated. As a result, when a film thickness is measured by using the region, an influence by a state in a difference in level can be avoided; in addition, in the case of visible light irradiation, an influence by a multiple reflection can be avoided; a film thickness of a selective growth film 7 in the contact hole 11 can be measured with high accuracy.